

PHASE CONTROL SCR

25TTS08

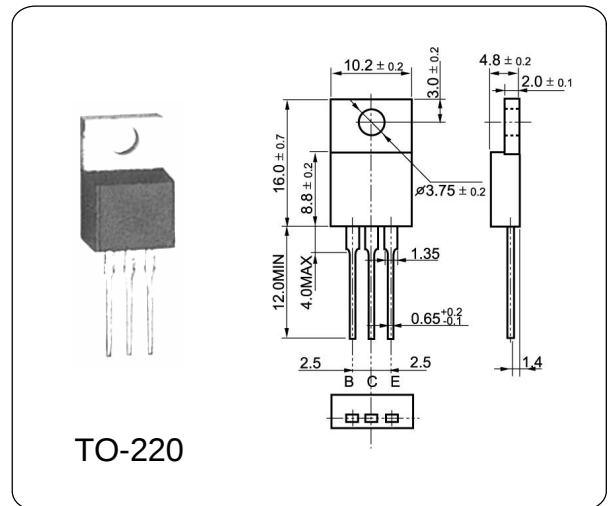
Description / Features

The 25TTS08 of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

Typical applications are in input rectification (softstart) and these products are designed to be used with International Rectifier input diodes, switches and output rectifiers which are available in identical package outlines.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Typ	Unit
Repetitive peak off-state voltages	V_{DRM} V_{RRM}	800	V
Average on-state current	$I_{T(AV)}$	16	A
RMS on-state current	$I_{T(RMS)}$	25	A
Non-repetitive peak on-state current	I_{TSM}	300	A
Max. Operating Junction Temperature	T_j	110	°C
Storage Temperature	T_{stg}	-45~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Repetitive peak off-state voltages	V_{DRM} V_{RRM}		—	800	—	V
Average on-state current	$I_{T(AV)}$	half sine wave; $T_{mb} < 103$ °C	—	16	—	A
RMS on-state current	$I_{T(RMS)}$	all conduction angles	—	25	—	A
On-state voltage	V_{TM}	@16A, $T_j = 25$ °C	—	—	1.25	V
Holding current	I_H	$V_D = 12$ V; $I_{GT} = 0.1$ A	—	—	100	mA
Latching current	I_L	$V_D = 12$ V; $I_{GT} = 0.1$ A	—	—	200	mA
Gate trigger current	I_{GT}	$V_D = 12$ V; $I_T = 0.1$ A	—	—	45	mA
Gate trigger voltage	V_{GT}	$V_D = 12$ V; $I_T = 0.1$ A	—	—	2.0	V